

TRIACS

AC03DJM, AC03DJM-Z, AC03FJM, AC03FJM-Z

3 A MOLD TRIAC

DESCRIPTION

The AC03DJM and AC03FJM are all diffused mold type TRIAC granted RMS On-state current 3 Amps, with rated voltage up to 600 volts.

FEATURES

- Small and surface mount package.
- 30 A Surge Current
- Less holding current distribution provides free application design.

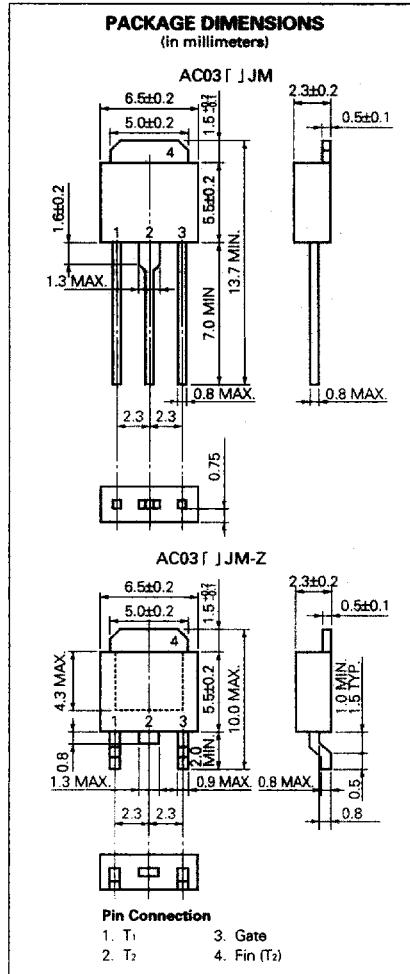
QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

APPLICATIONS

Temperature Control, Light Dimmer Control, AC Motor Speed, Control Electric Jar, Electric Lamp Starter, Various Solid State Switch, etc.



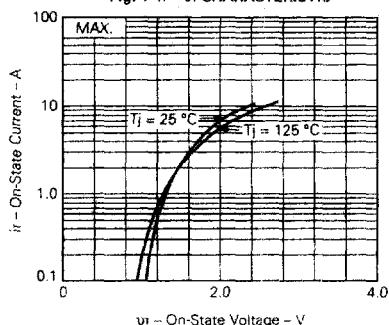
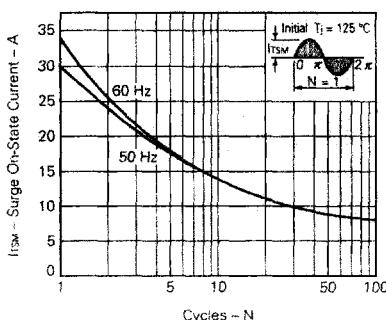
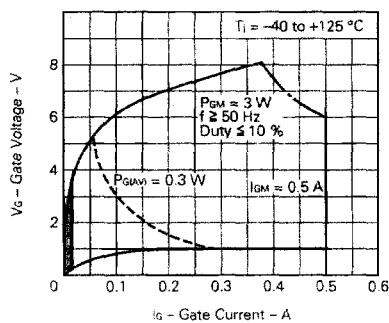
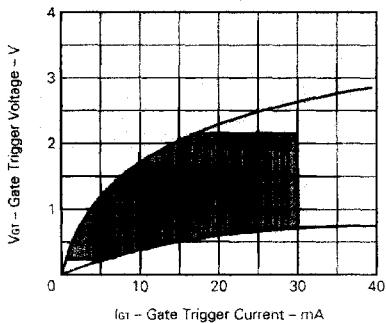
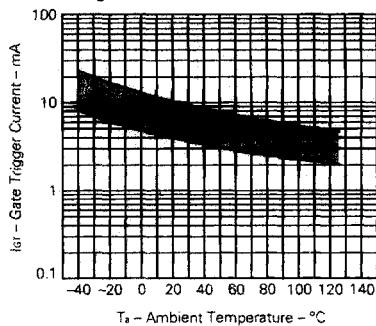
ABSOLUTE MAXIMUM RATINGS ($T_{\theta} = 25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	AC03DJM	AC03FJM	UNIT	NOTE
Repetitive Peak Off-State Voltage	V_{DRM}	400	600	V	
Non-repetitive Peak Off-State Voltage	V_{DSS}	500	700	V	
RMS On-State Current	I_{TRMS}	$3 \text{ (} T_c = 110^{\circ}\text{C) }$		A	See Fig. 11
Surge On-State Current	I_{SM}	$30 \text{ (} 50 \text{ Hz 1 cycle) }$		A	See Fig. 2
Fusing Current	$\int i^2 dt$	$4.0 \text{ (} 1 \text{ ms} \leq t \leq 10 \text{ ms) }$		A^2s	
Peak Gate Power Dissipation	P_{GM}	$3 \text{ (} f \geq 50 \text{ Hz, Duty} \leq 10\% \text{) }$		W	
Average Gate Power Dissipation	P_{GAVI}	0.3		W	
Peak Gate Current	I_{GM}	$\pm 0.5 \text{ (} f \geq 50 \text{ Hz, Duty} \leq 10\% \text{) }$		A	
Junction Temperature	T_j	$-40 \text{ to } +125$		$^{\circ}\text{C}$	
Storage Temperature	T_{stg}	$-55 \text{ to } +150$		$^{\circ}\text{C}$	

ELECTRICAL CHARACTERISTICS ($T_{\theta} = 25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	NOTE
Peak Off-State Current	I_{DM}	$V_{DM} = V_{DRM}$		—	—	100	μA	
Peak Off-State Current	I_{DM}	$T_j = 125^{\circ}\text{C}, V_{DM} = V_{DRM}$		—	—	1	mA	
On-State Voltage	V_{TM}	$I_{TM} = 5 \text{ A}$		—	—	1.8	V	See Fig. 1
Gate-trigger Current	I_{GT}	$V_{DM} = 12 \text{ V, } R_L = 30 \Omega$	$T_2+, G+$	—	—	12	mA	See Fig. 4, 5, 7
			$T_2-, G+$	—	—	—		
			$T_2-, G-$	—	—	12		
			$T_2+, G-$	—	—	12		
Gate-trigger Voltage	V_{GT}	$V_{DM} = 12 \text{ V, } R_L = 30 \Omega$	$T_2+, G+$	—	—	1.5	V	See Fig. 4, 6, 8
			$T_2-, G+$	—	—	—		
			$T_2-, G-$	—	—	1.5		
			$T_2+, G-$	—	—	1.5		
Gate Non-Trigger Voltage	V_{GO}	$T_j = 125^{\circ}\text{C, } V_{DM} = 1/2 V_{DRM}$		0.2	—	—	V	
Holding Current	I_H	$V_{DM} = 24 \text{ V, } I_{TM} = 5 \text{ A}$		—	7	—	mA	
Critical Rate of Rise of Off-State Voltage	dV/dt	$T_j = 125^{\circ}\text{C, } V_{DM} = 2/3 V_{DRM}$		—	100	—	$\text{V}/\mu\text{s}$	
Commutating dV/dt	$(dV/dt)_C$	$T_j = 125^{\circ}\text{C}$ $(dV/dt)_C = -1.6 \text{ A/ms}$ $V_{DM} = 400 \text{ V}$		5	—	—	$\text{V}/\mu\text{s}$	
Thermal Resistance	$R_{Th(j-e)}$	Junction to Case		—	—	4	$^{\circ}\text{C/W}$	See Fig. 13
Thermal Resistance	$R_{Th(j-a)}$	Junction to Ambient*		—	—	62.5	$^{\circ}\text{C/W}$	AC03DJM-Z AC03FJM-Z

* Mounted on ceramic substrate of $7.5 \text{ cm}^2 \times 0.7 \text{ mm}$.

TYPICAL CHARACTERISTICS ($T_a \approx 25^\circ\text{C}$)Fig. 1 $i_T - v_T$ CHARACTERISTICFig. 2 I_{TSM} RATINGFig. 3 $V_G - I_G$ RATINGFig. 4 $V_{GT} - I_{GT}$ CHARACTERISTICFig. 5 $I_{GT} - T_a$ TYPICAL DISTRIBUTIONFig. 6 $V_{GT} - T_a$ TYPICAL DISTRIBUTION